

WEST - (resistor.wsp)

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Drafts

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L1: (82) (fin adj field adj effect adj transistor) or finfer

L2: (32) 1 and trench52

L3: (25) 2 and (grow53 or regrow53)

L4: (4) 2 and trench52.clm.

L5: (13) 1 and (trench52 or hole51 or via51).clm.

(0) ("(thinadjfilm)nearresistor").PN.

(0) ("(thinadjfilm)nearresistor").PN.

(150130) thin adj film

(14857) (thin adj film) and resistor

(2054) ((thin adj film) and resistor) and ((thin adj film) ne

(1735) (((thin adj film) and resistor) and ((thin adj film) r

(801) (((thin adj film) and resistor) and ((thin adj film) r

(499) (((thin adj film) and resistor) and ((thin adj film) r

(124) (((thin adj film) and resistor) and ((thin adj film) r

(34) (((thin adj film) and resistor) and ((thin adj film) r

(98) (((thin adj film) and resistor) and ((thin adj film) r

Doc: VEPART000006

DocType: 01

DocName: 1 and (trench52 or hole51 or via51).clm.

Properties

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	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C				
1					US 20040048424	20040311	16	Method of forming an N channel and P channel F	438/154			Wu, Chung Cheng et al.						
2					US 20040046227	20040311	23	Semiconductor device	257/500			Ono, Mizuki et al.						
3					US 20040036118	20040226	48	Concurrent Fin-FET and thick-body device fabri	257/347			Abadeer, Wagdi W. et al.						
4					US 20030141569	20030731	13	Fin-type resistors	257/536	257/379; 257/E21.00		Fried, David M. et al.						
5					US 6720231 B2	20040413	13	Fin-type resistors	438/382	257/722; 438/238;		Fried, David M. et al.						
6					US 6709982 B1	20040323	12	Double spacer FinFET formation	438/696	438/304; 438/596		Buynoski, Matthew S. et al.						
7					US 6706571 B1	20040316	15	Method for forming multiple structures in	438/157	438/283; 438/286;		Yu, Bin et al.						
8					US 6580137 B2	20030617	33	Damascene double gated transistors and related	257/401	257/407; 257/E21.40		Parke, Stephen A.						
9					US 6525403 B2	20030225	20	Semiconductor device having MIS field effect	257/618	257/329; 257/330;		Inaba, Satoshi et al.						
10					US 6521502 B1	20030218	8	Solid phase epitaxy activation process for	438/305	438/528		Yu, Bin						
11					US 6403434 B1	20020611	10	Process for manufacturing MOS trans	438/300	257/E21.16 6;		Yu, Bin						

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